We claim:

1. A heating body of an epitaxial growth device configured to heat a substrate, comprising at least one supporting base and at least one tray,

wherein the at least one supporting base is provided with at least one temperature control channel, the at least one temperature control channel is hollow and penetrates through the at least one supporting base along a horizontal axis of the epitaxial growth device;

the at least one tray is mounted on the at least one supporting base to support the substrate;

the at least one temperature control channel is configured to accommodate a temperature control medium, and the temperature control medium is able to be input and output via two ends of the at least one temperature control channel respectively, so as to control an environment temperature of the at least one tray.

2. The heating body of the epitaxial growth device of claim 1, wherein the at least one temperature control channel is proximal to an edge of the at least one tray, and along a direction perpendicular to a surface of the at least one supporting base, a part of a projection of the at least one temperature control channel is on the at least one tray.

3. The heating body of the epitaxial growth device of claim 1, wherein the at least one supporting base comprises one temperature control channel, and a part of the temperature control channel is in a ring shape.

4. The heating body of the epitaxial growth device of claim 3, wherein the temperature control channel successively comprises a first segment, a second segment, and a third segment, which are in communication with each other; the second segment is in a ring shape, and the second segment is proximal to an edge of the at least one tray.

5. The heating body of the epitaxial growth device of claim 1, wherein the at least one supporting base comprises two temperature control channels, and the two temperature control channels are disposed corresponding to two sides of the at least one tray respectively.

6. The heating body of the epitaxial growth device of claim 5, wherein the at least one supporting base comprises an air floating channel which is located between the two

temperature control channels, and the two temperature control channels are symmetrically arranged with the air floating channel as an axis.

7. The heating body of the epitaxial growth device of claim 1, wherein the at least one supporting base comprises a first portion and a second portion, and the at least one temperature control channel is defined by the first portion and the second portion.

8. The heating body of the epitaxial growth device of claim 1, wherein the number of at least one supporting base is multiple, the multiple supporting bases are sequentially arranged along a direction perpendicular to the axis of the epitaxial growth device.

9. The heating body of the epitaxial growth device of claim 8, wherein the heating body further comprises a supporting member disposed between adjacent two adjacent supporting bases.

10. An epitaxial growth device, comprising the heating body of any one of claims 1 to 9.